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Please amend the claims as follows:

40. (Amended) A semiconductor device, comprising:

a first active region;

a second active region; [and]

a third active region disposed between said first and second active regions; and

first, second and third contacts connected respectively to said first, second and third active regions;

said first and second active regions being symmetrically self-aligned.

45. (Amended) A device as recited in claim 42, comprising:

said base having a lower and an upper ledge; and

said third contact comprising:

a first base contact formed on said upper ledge self-aligned with said emitter; and

a second base contact formed on said lower ledge self-aligned with said collector.

46. (Amended) A device as recited in claim 42, comprising:

said base having a ledge;

[a first base] said third contact formed on said ledge self-aligned with said emitter.

47. (Amended) A device as recited in claim 46, [comprising] wherein:

said base [having] has ledges on opposing sides; and

said third contact comprises:

[said] a first base contact formed from a front side of said device; and

a second base contact formed opposing said first base contact on said ledge self-aligned with said collector and formed from a back side of said device.

50. (Amended) A device as recited in claim 42, [comprising] wherein:

said base layer [having] ~~has~~ a lower ledge and an upper ledge; and
said third contact comprises:

a first base contact formed on said upper ledge; and

a second base contact formed on said lower ledge.